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Characterizing the local vectorial electric field near an atom chip using Rydberg-state spectroscopy

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We use the sensitive response to electric fields of Rydberg atoms to characterize all three vector components of the local electric field close to an atom-chip surface. We measured Stark-Zeeman maps of $S$ and $D$ Rydberg states using an elongated cloud of ultracold rubidium atoms (temperature $T \sim 2.5 \, \mu$K) trapped magnetically 100 $\mu$m from the chip surface. The spectroscopy of $S$ states yields a calibration for the generated local electric field at the position of the atoms. The values for different components of the field are extracted from the more complex response of $D$ states to the combined electric and magnetic fields. From the analysis we find residual fields in the two uncompensated directions of $0.0 \pm 0.2$ and $1.98 \pm 0.09$ $\text{V/cm}$. This method also allows us to extract a value for the relevant field gradient along the long axis of the cloud. The manipulation of electric fields and the magnetic trapping are both done using on-chip wires, making this setup a promising candidate to observe Rydberg-mediated interactions on a chip.

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I. INTRODUCTION

An important challenge in the implementation of quantum information protocols and in quantum simulation is to create strong, long-range, tunable, and switchable interactions. Rydberg atoms have exaggerated properties, such as very large electrical polarizabilities and (induced) dipole moments [1]. These characteristics make them very good candidates as mediators of the needed interactions and are the reason why they are now being widely pursued as systems for quantum information science using various approaches, including cavity quantum electrodynamics [2], trapped ions [3], and neutral atoms [4–6]. Among these approaches the combination of atom chips with neutral atoms offers unique opportunities to study quantum-degenerate gases [7] with the advantage of having a compact system that allows the efficient manipulation of quantum gases. Due to their sensitive response to electric fields, Rydberg atoms are also used as a tool for electrometry [8]. One of the disadvantages of using Rydberg atoms in an atom-chip experiment is the presence of spatially inhomogeneous electric fields [9–11]. These fields are produced, e.g., by adsorbates (deposited) on the surface of the chip [10–12] or by a voltage drop across current-carrying wires on the chip. Due to the large polarizability of Rydberg atoms and their proximity to a surface, the coherence of the excitation will be limited by these stray electric fields. This makes the observation of Rydberg-mediated interactions in such systems a challenge. A detailed characterization of the mentioned stray electric fields is therefore crucial.

Here, we employ two-photon Rydberg Stark-Zeeman spectroscopy of a cloud of magnetically trapped ultracold $^{87}$Rb atoms (temperature $T \sim 2.5 \, \mu$K) to characterize the local electric fields from an atom-chip surface ($\sim 100 \, \mu$m distance). An additional auxiliary electric field is generated at the location of the atoms by applying a voltage to an on-chip wire adjacent to the magnetic trapping wire. We show that it is possible to characterize the two uncompensated vector components of the local electric field (the third component is compensated by the auxiliary electric field) by a careful analysis of the measured Stark-Zeeman spectra of $S$ and $D$ states. The results are consistent with the calculated structure of Rydberg states in combined magnetic and electric fields. We also characterize the electric field gradient along the long axis of the cloud.

This paper is structured as follows. In Sec. II we summarize our calculations of $D$-state Stark-Zeeman maps for different field configurations and show how these are affected by residual fields in different directions. The experimental setup and data acquisition procedure are explained in Sec. III, followed by the main experimental results and a comparison with the calculations described in the previous section. A summary of the main results is given in Sec. IV.

II. STARK MAP SIMULATIONS

To compare our experimental results to theory, we need to calculate the Rydberg energies and eigenstates in combined electric and magnetic fields, with an a priori unknown angle between the two. To this end, we first calculate field-free radial Rydberg wave functions, then include the electric field by calculating the matrix elements of the electric-field operator and diagonalizing the result to obtain Stark eigenstates and eigenenergies, and, finally, take into account the magnetic field as a small perturbation in the Hamiltonian to obtain combined Stark-Zeeman maps. We have verified that the results of our calculations are consistent with results from open-source Rydberg calculator packages [13,14] that have recently become available.

In more detail, the calculation of the desired Stark-Zeeman maps starts from the binding energies $E_b = -\frac{R}{[2(n - \delta)^2]}$ of the field-free Rydberg states, given by the experimentally determined quantum defects $\delta_{n,l,j}$ of $^{87}$Rb for $S$ and $D$ states [15], $P$ states [16], $F$ states [17], and $G$ states [18] and the reduced Rydberg constant $R$ for $^{87}$Rb. Here, $n$ is the principal quantum number, $l$ is the orbital angular momentum, and $j$ is the total angular momentum of the valence electron. For $l > 4$ the quantum defect is negligibly small, and we set it to zero. Under field-free conditions, the Rydberg wave

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functions separate into a product of a radial wave function and a remaining function describing the electron spin and angular part of the wave function. The radial wave functions $\psi_{n,l,j}(r)$ are obtained numerically using the Numerov method [19,20], integrating the radial Schrödinger equation inward starting from the classically forbidden outer region of the Coulomb potential with an energy given by the above quantum defects and with a variable step size adapted to the changing spatial potential with an energy given by the above quantum defects from the classically forbidden outer region of the Coulomb integrals.

In an applied electric field, $m_j$ (corresponding to the projection of the angular momentum onto the electric-field direction) remains a good quantum number. The energies and eigenstates depend on $m_j$ and can be obtained for each $m_j$ separately. To this end, a set of all states with energies around the energy of interest is selected (typically ~1000 states) for each $m_j$, and a finite-size matrix is set up with the diagonal elements given by the (field-free) energies and the off-diagonal elements given by the matrix elements of the electric-field operator. The latter are obtained using the above radial wave functions for the radial matrix elements and the Clebsch-Gordan coefficients for the angular part. The resulting matrix is diagonalized, yielding a Rydberg Stark map of energies and eigenvectors for each $m_j$ as a function of electric-field strength $E$.

To account for magnetic fields of a few gauss, we limit ourselves to a single value for $n$, $l$, and $j$ (consistent with our magnetic trap) and the corresponding set of $(2j + 1)$ basis states distinguished by their value of $m_j$ (with the quantization axis along the electric-field direction). The corresponding eigenenergies $E(n,l,j,m_j)$ yield a (diagonal) Stark Hamiltonian matrix within this manifold. Within this basis set the Zeeman Hamiltonian (with the magnetic field at an angle with respect to the electric field) is added as a perturbation, and the resulting matrix is again diagonalized to yield a Stark-Zeeman map of eigenvalues and eigenstates. This method works well as long as the Zeeman splittings are much below the fine-structure splitting (this is 560 MHz for the 28D state, so that the magnetic field should be below 100 G). The results of such a calculation are shown in Fig. 1.

From these calculations it is possible to analyze the character of each sublevel after a projection of the eigenbasis on the $B$ field direction. At zero electric field each sublevel is defined by the Zeeman shift. In Fig. 1(a) this means that each curve represents $m_j = 5/2,3/2,1/2,-1/2,-3/2,-5/2$ from top to bottom, respectively. In the case in which $E \parallel B$ [black curves in Fig. 1(a)] the analysis is trivial because the quantization axis is unambiguous; hence, each sublevel maintains its original character at any electric-field value. As a result the Stark shift (which depends only on the absolute value $|m_j|$) and Zeeman shift are simply additive.

The analysis is more complicated for the case when $E \perp B$. As the electric field is increased, the character of each state changes; for instance, the highest-energy state, $m_j = 5/2$ (along $B$) changes its character to a superposition of $m_j = -1/2$ and $m_j = +1/2$ (along $E$) at higher electric fields. The behavior at high electric fields can be intuitively understood as follows (we take the quantization axis along the electric field in the remainder of this paragraph). In the absence of a magnetic field the highest-energy level is twofold degenerate, with quantum numbers $m_j = \pm 1/2$. The other states, with larger $|m_j|$, are Stark shifted relatively far away (down) in energy. A small magnetic field orthogonal to the electric field couples electric-field eigenstates with $\Delta m_j = \pm 1$. This coupling is most effective between the two states with $|m_j| = 1/2$ (since these have $\Delta m_j = \pm 1$ and are degenerate in energy in the absence of a magnetic field). It splits up the upper two states into the symmetric and antisymmetric combinations of $m_j = -1/2$ and $m_j = +1/2$. The downshifted states, with larger $|m_j|$, are only weakly affected by the magnetic field (since the magnetic field does not couple within the pair with the same $|m_j| > 1/2$), and as a result for each $|m_j| > 1/2$ the two states are nearly degenerate in energy. This analysis is
important when setting the polarization of our lasers for the Rydberg excitation in order to select which state we excite in view of the selection rules. For the sake of simplicity we will use the zero-electric-field labeling (ZEL) to identify the various sublevels throughout this paper, even when the electric field has a nonzero value.

From Fig. 1(a), we see that in the case of perpendicular fields (red lines), \( \vec{E} \perp \vec{B} \), the energy of the two uppermost magnetic sublevels first decreases, followed by an increase in energy at higher fields, thus creating a dip in the Stark map. The size of this initial dip is very sensitive to additional (stray) electric fields. In Fig. 1(b) we illustrate this by showing four different configurations in which we varied the contributions of residual fields between 0 and 2 V/cm. These contributions were taken parallel to the magnetic field \( E_x \) and perpendicular to both the applied electric field and magnetic field \( E_y \); a sketch of the field geometry is shown in Fig. 2(a).

A stray field in the \( x \) direction of 2 V/cm already shows a total disappearance of the local minimum for the top state. More generally, the precise shape of the Stark-Zeeman map of the top two states is very sensitive to the strength of the electric-field components \( E_x \) and \( E_y \), enabling the characterization of these fields. The role of the magnetic field is relevant because its value defines the energy difference between each magnetic sublevel at zero electric field, which is the Zeeman shift. Moreover, Fig. 1(b) shows that this energy difference varies as the electric field is increased, revealing the importance of the magnetic-field configuration in the analysis of the data. Consequently, the combination of electric and magnetic fields is crucial for the full characterization of residual unknown stray electric fields.

**III. EXPERIMENTAL RESULTS**

The experimental setup employs an atom chip [7] to trap and cool a cloud of Rb atoms in vacuum at a distance of \( \sim 100 \mu m \) from a set of microfabricated gold wires [see Fig. 2(a)]. Our setup and methods have been described in detail elsewhere [23–25]. In brief, we start from a cloud of \( ^{87}\text{Rb} \) atoms loaded in a mirror-magneto-optical trap (MMOT) with the mirror formed by the atom chip, a patterned 2-\( \mu m \)-thick gold layer on a 16 \( \times \) 25 mm\(^2\) silicon substrate. These atoms are then optically pumped to the \( |S_{1/2}\rangle \) state and transferred to a magnetic trap where they are cooled down to \( \sim 2.5 \mu K \) using rf-induced evaporative cooling. The magnetic trapping is done using a 125-\( \mu m \)-wide on-chip Z-shaped wire [wire labeled 5 in Fig. 2(a)] carrying a current of 1 A. This final trap is elongated (cigar shaped), with trap frequencies \( \omega_x \), \( \omega_y \), and \( \omega_z \) being 46 Hz and \( \omega_y \) being 860 Hz. The bottom of the trap is at \( B = 3.41 \) G (corresponding to an rf frequency of 2.39 MHz). After evaporation there are approximately \( 10^3 \) atoms in the trap. At \( T = 2.5 \mu K \) the calculated cloud size (FWHM) is 6.8 \( \mu m \) in the radial directions and 127 \( \mu m \) in the longitudinal direction. The temperature of the cloud is extracted from a time-of-flight (TOF) measurement in which the expansion of the cloud is measured as a function of the time after it was released.

This setup has been extended with a two-photon Rydberg excitation scheme. We excite atoms from the \( 5S_{1/2} \) ground state to a Rydberg level via the intermediate state \( 5P_{3/2} \) using a 780-nm infrared laser and a 480-nm blue laser in a 7-ms pulse during magnetic trapping. Both lasers are aligned along the long \( \langle x \rangle \) axis of the magnetic trap, and the lasers are frequency narrowed and stabilized by locking them to a home-built reference cavity that is described in detail elsewhere [26]. With this scheme we reach a linewidth \( \leq 10 \) kHz for both lasers.

For the Rydberg excitation we use blue and infrared powers of 90 mW and \( \sim 0.5 \mu W \), respectively. In order to increase the two-photon Rabi frequency the coupling blue beam is focused down to a waist of 90 \( \mu m \). This leads to a blue Rabi frequency at full power of \( \Omega_c \approx 10 \) MHz for the \( 5P_{3/2}\rightarrow 30S_{1/2} \) transition. The infrared beam waist at the position of the atoms is 520 \( \mu m \). The detuning to the intermediate \( 5P_{3/2} \) state is...
100 MHz towards the blue for the 780-nm laser to reduce losses due to intermediate-state scattering. Finally, after the Rydberg excitation pulse, the remaining ground-state atoms (Rydberg atoms are lost during the excitation pulse by decay into nontrapped states) are released and detected after a time of flight of several milliseconds using absorption imaging.

By scanning the blue frequency across resonance and measuring the number of remaining atoms as a function of this frequency we obtain Rydberg loss spectra. In order to change the electric field at the position of the atoms we pulse a voltage during the Rydberg excitation. This voltage is applied to one of the on-chip wires [wire 4 in Fig. 2(a)] during the magnetic-trapping and Rydberg-excitation phase. The wire we use to generate the electric field at the position of the atoms (wire 4) is 10 μm wide, and the distance of its center from the nearby edge of wire 5 is 35 μm. All the other wires (except wires 4 and 5) and the silicon substrate are kept floating. It is important to note that all the wires have a finite resistance (on the order of 10 kΩ) to each other via the silicon substrate [24]. Thus, as we apply a voltage to wire 4, most of the chip surface shifts voltage towards the voltage of wire 4. The exception is wire 5, where the voltage (and current) is pinned by the current supply attached to it. To characterize the voltage distribution across the chip surface we use the fact that the resulting voltages on most of the wires are accessible outside the vacuum system via a multipin vacuum feedthrough.

We have measured these voltages under operating conditions (i.e., with current for magnetic trapping applied to wire 5 and varying the voltage on wire 4) and found that the voltage on all the wires (with the already noted exception of wire 5) shifts roughly linearly with the voltage on wire 4. These voltages were used to calculate the direction of the applied electric field (the direction of the μ axis in Fig. 2). A further detail that is relevant is that we found a slight asymmetry in the measured voltages on the other wires as the sign of the voltage difference between wire 4 and the center of wire 5 changed (see Sec. III A).

A. Stark map of the S state

In order to calibrate the relation between the applied voltage and the locally applied electric field at the position of the atoms we first measured a Stark map of the 30S1/2 state by taking Rydberg loss spectra for various applied voltages. We set the polarization of the blue and infrared lasers to be σ− and σ+, respectively. We fitted a Gaussian to each Rydberg spectrum in order to obtain the amplitude, position, and FWHM of the loss feature. The resonance position and width of the Rydberg feature are plotted as a function of the applied voltage in Fig. 3. The vertical bars represent the FWHM of each feature in the spectrum. As expected, in the presence of electric field gradients (see Sec. III C), the feature gets broader as we increase the applied field. We found that the voltages on the on-chip wires are slightly asymmetric around the applied voltage on wire 4 $V_{ap}$. A possible explanation for this behavior is a leakage current between the chip wires that is slightly asymmetric in the voltage difference between the wires. This produces an asymmetry in the shift in frequency around $\pm 1.4$ V. To account for this we fit separate quadratic functions with a shared apex to the data in order to produce a voltage-to-field relation. The quadratic functions smoothly connect at the top but have different curvatures. The resulting fits are shown in Fig. 3. Using the known polarizability of the 30S state [27], we can extract a relation between the applied voltage and the field generated at the position of the atoms using

$$\Delta = -\frac{1}{2} \alpha_{30S} E^2,$$

where $\alpha_{30S} = 1.39$ MHz/(V/cm)$^2$ is the polarizability of the 30S state and $\Delta$ is the energy shift of the Rydberg feature produced by the presence of an electric field $E$. Using these two different fits, we obtained a field-voltage relation of the form

$$E_{ap} = c_1 (V_{ap} - V_0).$$

Here, $E_{ap}$ is the applied field at the position of the atoms, and $c_1$ are two different coefficients depending on which side of the parabola the applied field is: $c_1 = 12.4$ cm$^{-1}$ and $c_1 = 16.4$ cm$^{-1}$ for $V_{ap} > -1.37$ V and $V_{ap} < -1.37$ V, respectively. $V_0 = -1.37$ V is the offset voltage we get for which the Stark shift is minimal. This voltage is consistent with the inferred voltage at the center of the trapping wire [wire 5 in Fig. 2(a)] produced by the current we send through it to generate the magnetic trap. Note that a small stray field along the direction of $E_{ap}$ would lead to a small shift of $V_0$ in the Stark map. In contrast, stray fields in the other two directions (orthogonal to $E_{ap}$) lead to a vertical energy offset $-\frac{1}{2} \alpha_{30S} (E_x^2 + E_y^2)$ in the Stark map of the S state that does not discriminate between $E_x$ and $E_y$ and that would require an absolute frequency reference to calibrate.

B. Stark map of the D state

The knowledge of the applied electric field at the position of the atoms allows us to measure a calibrated Stark map of the 28D3/2 state. To do so we set the polarization of the blue and infrared beams to be linearly polarized in such a
FIG. 4. The 28D_{5/2} state Stark map of two different sublevels: The top and bottom curves are the \( m_j = 5/2 \) and \( m_j = 3/2 \) sublevels (ZEL), respectively. The color scale indicates the normalized number of atoms, normalized to the number of atoms measured when the Rydberg excitation lasers are off resonance. The measurements were taken outside the dark red area. We deliberately saturated the upper sublevel in order to be able to see the other one, which has a much smaller coupling strength. The white lines are the resulting fitted curves for the resonance position of each sublevel where the parallel and perpendicular electric fields are used as fitting parameters (from the fit we get \( E_r = 0 \) V/cm and \( E_v = 1.98 \) V/cm, respectively; see main text for details).

way that we are able to see both the \( m_j = 5/2 \) and \( m_j = 3/2 \) states (ZEL). The resulting Stark-Zeeman map is shown in Fig. 4. We used Eq. (2) to transform the \( x \) axis from an applied voltage to an applied electric field at the position of the atoms. We fitted two Gaussians to each spectrum for a given applied field and extracted the main properties of the two features: amplitude, FWHM, and position. The comparison of the resonance position obtained from the data with the calculated ones gives us values for the components of the stray field \( E_i \) (parallel to \( \vec{B} \)) and \( E_v \) (perpendicular to \( \vec{B} \) and \( \vec{E}_{ap} \)). The analysis is based on the shape and the size of the initial dips in the Stark map (for applied fields \( \leq 10 \) V/cm) which strongly depend on the stray field configuration [see Fig. 1(b)]. Considering the values obtained for the electric-field components, we can estimate to what extent the FWHM of each feature is limited by field gradients.

From the Stark-Zeeman map in Fig. 4 we already see the initial dip in the energy shift of the resonance of both states, so we can immediately set an upper limit to the field in the parallel direction of \( E_i \lesssim 2 \) V/cm. The coupling strength of the \( m_j = 3/2 \) state is much weaker than that of the \( m_j = 5/2 \) (ZEL), so we have to strongly saturate the latter in order to see both at the same time. The weak feature has a much more prominent dip as a function of electric field than the strong one. Therefore, the simultaneous use of the resonance positions of both states results in a more accurate analysis of the data. However, since the \( m_j = 5/2 \) state is strongly saturated, it is not possible to extract an accurate value for the resonance position of the Rydberg feature. In order to get a better data set for this state we set the blue and infrared beams to be \( \sigma_+ \) polarized, so only the transition to the \( m_j = 5/2 \) state (ZEL) is allowed by selection rules. Because this state has a strong coupling, it is possible to investigate its behavior also at higher electric fields without losing the signal. The resulting Stark-Zeeman map is shown in Fig. 5(a). These data are combined with the previously measured \( m_j = 3/2 \) state (ZEL) data and fitted to the calculated Stark-Zeeman map [Fig. 1(b)] with the residual electric fields \( E_i \) and \( E_v \) as fitting parameters. For the fit we use only data for fields \( E_{ap} < 15 \) V/cm, from which we obtain \( E_i = 0.0 \pm 0.2 \) V/cm and \( E_v = 1.98 \pm 0.09 \) V/cm.1 The resulting fitted curves are shown on top of the measured Stark-Zeeman map as white lines in Figs. 4 and 5(a).

Although the resulting fitted curves show excellent agreement with both sublevels at low field values, \( E_{ap} < 10 \) V/cm,

1The stated uncertainties in the fields, \( \Delta E_i \) and \( \Delta E_v \), are calculated assuming that the reduced \( \chi^2 \) value of the model is 1, \( \chi^2 = 1 \). Thus, \( \Delta E_i \) and \( \Delta E_v \) are obtained by allowing the \( \chi^2 \) value to increase by 1 from its minimum value. The more usual approach of extracting the uncertainty from the inverse covariance matrix on the basis of the curvatures at the minimum of \( \chi^2 \) is not applicable because the dependence of \( \chi^2 \) on \( E_v \) was found to be nonquadratic [28].
there is a discrepancy at high field values, $E_{ap} \approx 20$ V/cm [see Fig. 5(a)]. We have verified that the frequency difference between the observed bump at $E_{ap} = 20$ V/cm and the observed dip at $E_{ap} = 5$ V/cm is reproducible and not affected by slow drifts in the experimental frequency calibration. This was done by measuring the frequencies of the observed bump at $E_{ap} = 20$ V/cm and the observed dip at $E_{ap} = 5$ V/cm directly after one another and confirming their vertical spacing in Fig. 5(a). One source for a reduction in the peak frequency shift at 20 V/cm is the differential ac Stark shift of the Rydberg level as the character of the state changes with increasing applied electric field. We calculated this to give a modest contribution, a downshift in frequency of $\sim 0.5$ MHz at $E_{ap} = 20$ V/cm. In short, the discrepancy between our calculation and the experimental results around $E_{ap} = 20$ V/cm may be due to a combination of factors and is still under investigation. This discrepancy does not affect the determination of $E_r$ and $E_c$ because it is visible only at high field values ($E_{ap} > 15$ V/cm), where small residual fields do not play a role.

C. Electric field gradients

We now focus on possible gradients in the electric field as a source of broadening in the experimental spectra. Already from the calculations we can conclude that in the areas where the Stark shift has an extremum as a function of field the applied electric field. We calculated this to give a modest contribution, a downshift in frequency of $\sim 0.5$ MHz at $E_{ap} = 20$ V/cm. In short, the discrepancy between our calculation and the experimental results around $E_{ap} = 20$ V/cm may be due to a combination of factors and is still under investigation. This discrepancy does not affect the determination of $E_r$ and $E_c$ because it is visible only at high field values ($E_{ap} > 15$ V/cm), where small residual fields do not play a role.

Another reason that might explain the difference between the model and the experimental data at low temperatures is the omission of density effects. At low temperatures there is an important increase in density which means Rydberg-mediated interactions might be playing a role in the observed width. Our model does not consider this. However, the value of the gradient is set mainly by the slope of the curve which is set by higher-temperature data ($T > 2 \mu$K). In this area, the dominant mechanism of broadening is the effect of gradients, particularly along the long direction of the cloud. The investigation of Rydberg-mediated interactions and collective effects at lower temperatures and higher densities is the subject of further work and is beyond the scope of the present paper.

IV. CONCLUSIONS AND OUTLOOK

We characterized the vector components of the stray electric field close to the chip surface in our atom-chip experiment by comparing calculated $S$ and $D$ Stark-Zeeman maps with experimental data. We applied a voltage to one of the on-chip wires in order to generate a field at the position of the atoms. The field is characterized using a measured $S$-state Stark-Zeeman map, which is then used as a tool to calibrate the field axis of the $D$-state Stark-Zeeman map. The energy shift of $D$ states when applying an electric field is nontrivial and has an initial dip in energy. The minimum of this dip, and therefore the change in curvature, strongly depends on the values of stray electric fields along different directions. The
values of these field components are obtained by fitting the data to the simulated Stark-Zeeman map. We obtained values for the residual fields that are relatively small, namely, $E_x = 0.0 \pm 0.2$ V/cm and $E_y = 1.98 \pm 0.09$ V/cm. We attribute this observed residual field mainly to stray fields produced by rubidium adsorbates on the surface of the chip. In fact, the total stray field is about a factor of 2 lower than that observed at the same distance (100 \, \mu m) under similar conditions using electromagnetically induced transparency [10], where the field was attributed to rubidium adsorbates on the gold surface.

The lower value we observe may be due to the somewhat elevated temperature of the current-carrying gold wire in our system, which should lead to reduced Rb coverage. Another contribution to the electric field comes from the current-carrying wire. Within the wire the electric field is given by the current and the resistivity of the gold wire and is $\sim 1$ V/cm along the wire (in the $x$ direction). At the position of the atoms we calculate this to lead to a contribution of $\sim 0.4$ V/cm along the $x$ direction. Since from the 28$D$-state spectra we find $E_z = 0$ V/cm, this field is apparently compensated by other contributions to the residual field (likely the Rb adsorbates).

We also made use of the linear response of $D$ states to applied electric fields. In this region the Rydberg signal is symmetric, and the increase in linewidth as we increase the applied electric fields. In this region the Rydberg signal is symmetric, and the increase in linewidth as we increase the applied electric fields.

The next generation of chips is being designed in which the one-dimensional character has been demonstrated that the one-dimensional character has advantages when observing Rydberg-mediated interactions [29]. From this research we can conclude that atom-chip experiments are a promising tool for the study of Rydberg systems. The level of on-chip control over the electric fields demonstrated here is promising for the observation of Rydberg blockade and Rydberg-mediated interactions in ultracold gases trapped on a chip, which is relevant for quantum information science and technology in integrated and compact systems. The next generation of chips is being designed in which the on-chip control over the electric fields will be done using the electrometry process described in this paper.

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